

Erratum: Fowler-Nordheim electron tunneling in thin Si-SiO₂-Al structures [J. Appl. Phys. 52, 5710 (1981)]

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On Fig. 6, page 5716 the value of $m_{ox} = 1.03 m_e$ is incorrect, resulting from a calculation error. The correct value should be of the order of $0.5 m_e$. We would like to thank Dr. Z. Weinberg from IBM for observing this error, and notifying us.

Erratum: A kinetic study of the plasma-etching process. I. A model for the etching of Si and SiO₂ in C_nF_m/H₂ and C_nF_m/O₂ plasmas [J. Appl. Phys. 53, 2923 (1982)]

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The label for the horizontal axis of Fig. 11 is in error. The species symbols for CF₄ and H₂ should be exchanged so

that the fraction of CF₄ decreases from left to right and the fraction of H₂ increases from left to right.

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